

MA862

Silicon epitaxial planer type

For band switching

■ Features

- Two electrically independent elements incorporated
- Small diode capacity C_D
- Low forward dynamic resistance r_f
- Optimum for a band switching of tuner

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	Single	100	mA
	Double	75	mA/Unit
Operating ambient temperature	T_{opr}	– 25 to + 85	°C
Storage temperature	T_{stg}	– 55 to +150	°C

■ Electrical Characteristics (Ta= 25°C)

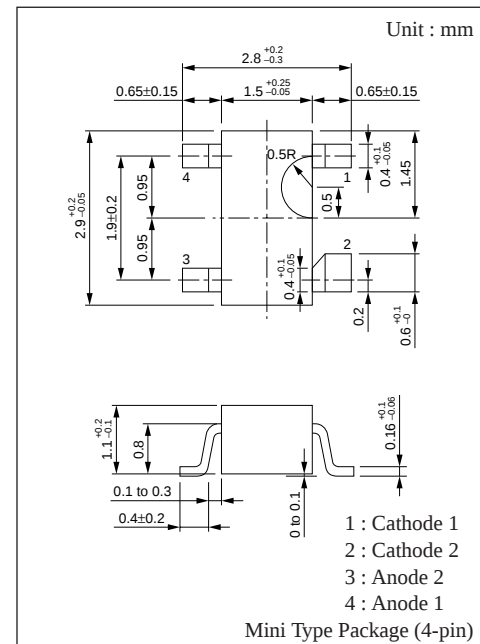
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 33V$			100	nA
Forward voltage (DC)	V_F	$I_F = 100mA$			1.0	V
Diode capacitance	C_t	$V_R = 6V, f = 1MHz$			1.2	pF
Forward dynamic resistance	r_f * 1	$I_F = 2mA, f = 100MHz$			0.65	Ω
	r_f * 2				0.98	Ω

Note 1 : Rated input/output frequency : 100MHz

2 : * 1 r_f measurement device : Nihon Koshuha MODEL TDC-121 A

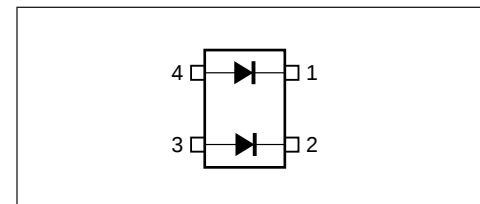
* 2 r_f measurement device : YHP 4191A RF IMPEDANCE ANALYZER

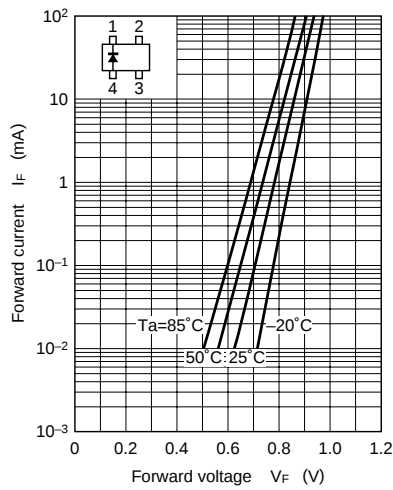
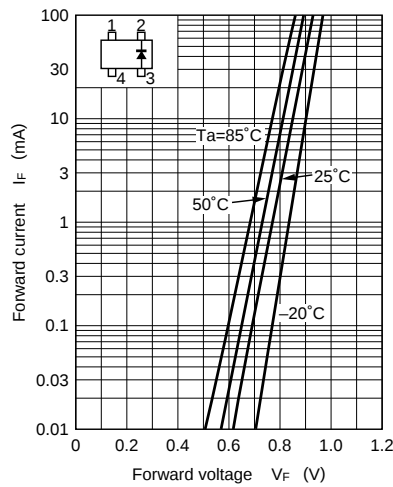
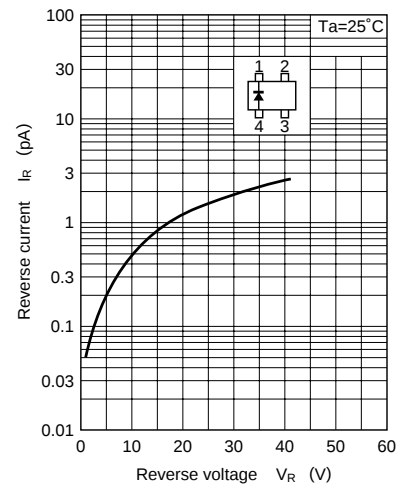
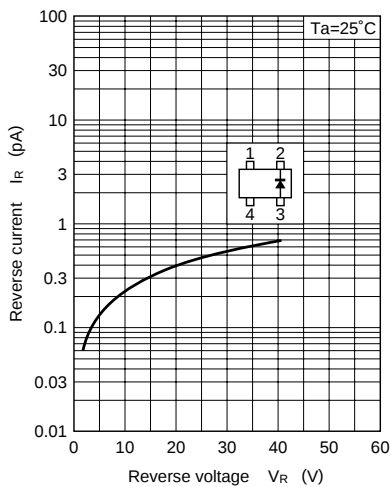
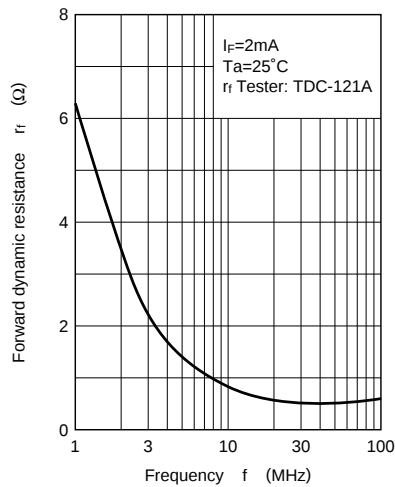
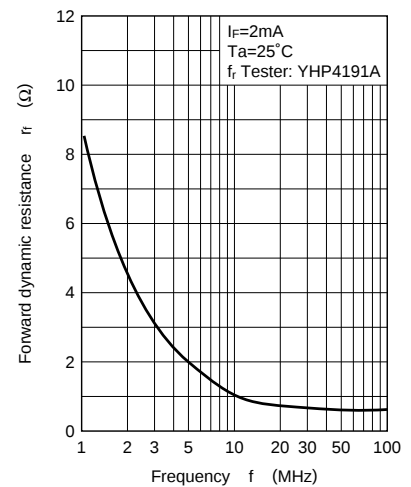
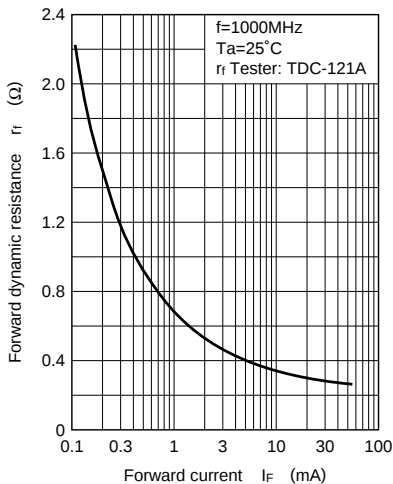
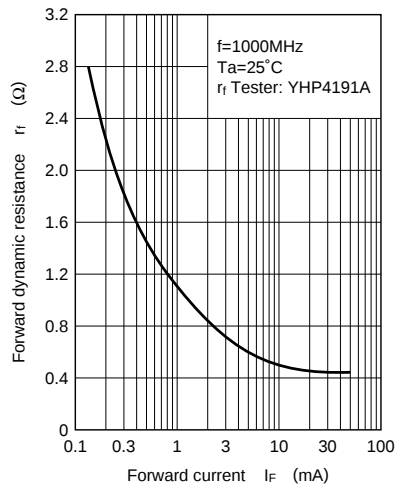
■ Marking



Marking Symbol : M11

■ Internal Connection



$I_F - V_F$ (1-4 pins) $I_F - V_F$ (2-3 pins) $I_R - V_R$ (1-4 pins) $I_R - V_R$ (2-3 pins) $r_f - f$  $r_f - f$  $r_f - I_F$  $r_f - I_F$  $C_D - V_R$ 